

Features

Applications

- Any frequency between 1 MHz and 220 MHz accurate to 6 decimal 10/40/100 Gbps Ethernet, SONET, SATA, SAS, Fibre places. For frequencies between 220.000001 and 725 MHz, see <u>SiT9367</u> datasheet. For standard frequencies up to 325 MHz, see ■ Telecom, networking, instrumentation, storage, servers SiT9365 datasheet.
 - Channel

- LVPECL, LVDS and HCSL output signaling
- 0.1 ps RMS phase jitter (random) for Ethernet applications
- Contact SiTime for ±10 ppm frequency stability
- Wide temperature ranges from -40°C to 105°C
- Industry-standard packages: 7.0 x 5.0 mm, 5.0 x 3.2 mm, 3.2 x 2.5 mm packages









Electrical Characteristics

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination show in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

Table 1. Electrical Characteristics – Common to LVPECL, LVDS and HCSL (All temperature ranges)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition		
	_			Frequency F	Range			
Output Frequency Range	f	1	-	220.000001	MHz	Accurate to 6 decimal places		
			F	requency St	tability			
Frequency Stability	F_stab	-10	Ι	+10	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations. Contact SiTime for ±10 ppm		
		-20	_	+20	ppm	Inclusive of initial tolerance, operating temperature, rated power		
		-25	_	+25	ppm	supply voltage and load variations.		
		-50	ı	+50	ppm			
First Year Aging	F_1y	Í	±1	-	ppm	At 25°C		
	Temperature Range							
Operating Temperature Range	T_use	-20	_	+70	°C	Extended Commercial		
		-40	_	+85	°C	Industrial		
		-40	ı	+95	°C			
		-40	ı	+105	°C	Extended Industrial		
				Supply Vol	tage			
Supply Voltage	Vdd	2.97	3.30	3.63	V			
		2.70	3.00	3.30	V			
		2.52	2.80	3.08	V			
		2.25	2.50	2.75	V			
			In	put Charact	eristics			
Input Voltage High	VIH	70%	ı	_	Vdd	Pin 1, OE		
Input Voltage Low	VIL	ı	ı	30%	Vdd	Pin 1, OE		
Input Pull-up Impedance	Z_in	_	100	-	kΩ	Pin 1, OE logic high or logic low		
			Ou	tput Charac	teristics			
Duty Cycle	DC	45	_	55	%			
			Sta	rtup and OF	E Timing			
Startup Time	T_start	ı	_	3.0	ms	Measured from the time Vdd reaches its rated minimum value.		
OE Enable/Disable Time	T_oe	-	-	3.8	μs	f = 156.25 MHz. Measured from the time OE pin reaches rated VIH and VIL to the time clock pins reach 90% of swing and high-Z. See Figure 6 and Error! Reference source not found.		



Table 2. Electrical Characteristics – LVPECL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
				Current C	onsun	nption	
Current Consumption	ldd	_	ı	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	_	ı	58	mA	OE = Low	
Output Disable Leakage Current	I_leak	_	0.15	-	μΑ	OE = Low	
Maximum Output Current	I_driver	-	ı	32	mA	Maximum average current drawn from OUT+ or OUT-	
	Output Characteristics						
Output High Voltage	VOH	Vdd-1.1	ı	Vdd-0.7	>	See Figure 2	
Output Low Voltage	VOL	Vdd-1.9	-	Vdd-1.5	V	See Figure 2	
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 3	
Rise/Fall Time	Tr, Tf	_	225	290	ps	20% to 80%, See Figure 3	
			Jitt	er – 7.0 x	5.0 mm	n Package	
RMS Period Jitter ^[1]	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)	T_phj	-	0.225	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		-	0.225	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C	
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	
		Jit	ter – 5.0	x 3.2 and	1 3.2 x 2	2.5 mm Packages	
RMS Period Jitter ^[1]	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)		-	0.225	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		-	0.225	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C	
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	

Notes:

Measured according to JESD65B



Table 3. Electrical Characteristics - LVDS

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
				Current	Consur	nption	
Current Consumption	ldd	ı	_	79	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	I	_	58	mA	OE = Low	
Output Disable Leakage Current	I_leak	ı	0.15	-	μΑ	OE = Low	
				Output C	haracte	eristics	
Differential Output Voltage	VOD	250	_	450	mV	See Figure 4	
VOD Magnitude Change	ΔVOD	ı	_	50	mV	See Figure 4	
Offset Voltage	VOS	1.125	_	1.375	V	See Figure 4	
VOS Magnitude Change	ΔVOS	ı	-	50	mV	See Figure 4	
Rise/Fall Time	Tr, Tf	ı	400	470	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 5.	
			Jitt	ter – 7.0 x	5.0 mn	n Package	
RMS Period Jitter ^[1]	T_jitt	I	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)	T_phj	-	0.215	0.265	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		-	0.215	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd level: includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C	
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	
		Ji	tter – 5.0	x 3.2 and	3.2 x 2	2.5 mm Packages	
RMS Period Jitter ^[1]	T_jitt	ı	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)	T_phj	ı	0.235	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		ı	0.235	0.320	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C	
		-	0.1	_	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	

Notes:
. Measured according to JESD65B



Table 4. Electrical Characteristics - HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
				Current	Consum	ption	
Current Consumption	ldd	-	_	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	_	58	mA	OE = Low	
Output Disable Leakage Current	l_leak	-	0.15	-	μΑ	OE = Low	
Maximum Output Current	I_driver	-	_	35	mA	Maximum average current drawn from OUT+ or OUT-	
				Output C	haracte	ristics	
Output High Voltage	VOH	0.60	_	0.90	V	See Figure 2.	
Output Low Voltage	VOL	-0.05	-	0.08	V	See Figure 2.	
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.80	V	See Figure 3.	
Rise/Fall Time	Tr, Tf	ı	360	465	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 3.	
			Jitt	er – 7.0 x	5.0 mm	Package	
RMS Period Jitter ^[3]	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)	T_phj	-	0.220	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		-	0.220	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°	
		ı	0.1	ı	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	
		J	itter – 5.0	x 3.2 and	1 3.2 x 2.	5 mm Packages	
RMS Period Jitter ^[3]	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V	
RMS Phase Jitter (random)	T_phj	_	0.230	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C	
		Ī	0.230	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C	
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.	

Notes:

3. Measured according to JESD65B

Table 5. Pin Description

Pin	Мар		Functionality
1	OE/NC	Output Enable	H ^[4] : specified frequency output
		(OE)	L: output is high impedance
		Non Connect (NC)	H or L or Open: No effect on output frequency or other device functions
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation
3	GND	Power	Vdd Power Supply Ground
4	OUT+	Output	Oscillator output
5	OUT-	Output	Complementary oscillator output
6	Vdd	Power	Power supply voltage ^[5]

Top View OE/NC 1 6 VDD NC 2 5 OUTGND 3 4 OUT+

Figure 1. Pin Assignments

Notes:

1. In OE mode, a pull-up resistor of 10 k Ω or less is recommended if pin 1 is not externally driven. A capacitor of value 0.1 μ F or higher between Vdd and GND is required. An additional 10 μ F capacitor between Vdd and GND is required for the best phase jitter performance



Table 6. Absolute Maximum Ratings

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Vdd	-0.5	4.0	V
VIH		Vdd + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	°C
Maximum Junction Temperature		130	°C
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	°C

Table 7. Thermal Considerations^[6]

Package	θ _{JA} , 4 Layer Board (°C/W)	θ _{JC} , Bottom (°C/W)
3225, 6-pin	80	30
5032, 6-pin	TBD	TBD
7050, 6-pin	52	19

Notes:

5. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 8. Maximum Operating Junction Temperature[7]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C
95°C	120°C
105°C	130°C

Notes:

6. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 9. Environmental Compliance

Parameter	Test Conditions	Value	Unit
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	G
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	G
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C
Moisture Sensitivity Level	MSL1 @ 260°C		
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V
Charge-Device Model ESD Protection	JESD220C101	750	V
Latch-up Tolerance	JESD78 Co	ompliant	



Waveform Diagrams

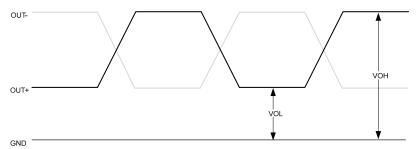


Figure 2. LVPECL/HCSL Voltage Levels per Differential Pin (OUT+/OUT-)

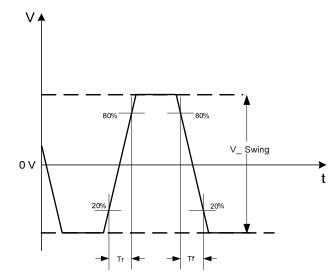


Figure 3. LVPECL/HCSL Voltage Levels Across Differential Pair



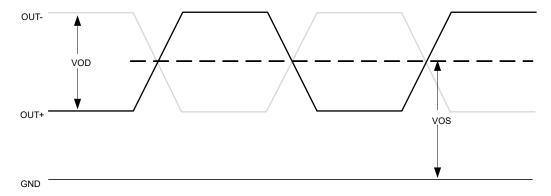


Figure 4. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)

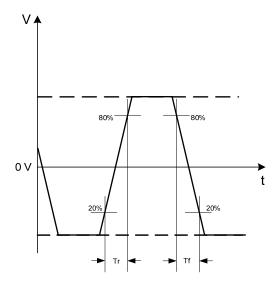


Figure 5. LVDS Differential Waveform

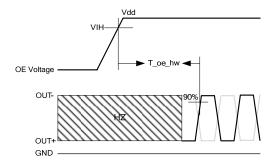


Figure 6. Hardware OE Enable Timing

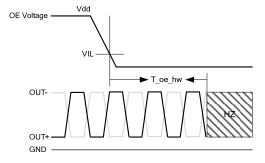


Figure 7. Hardware OE Disable Timing



Termination Diagrams

LVPECL:

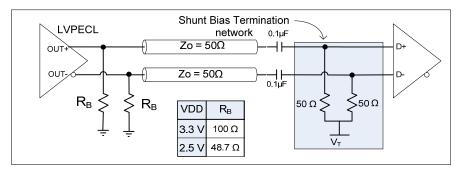


Figure 8. LVPECL with AC-coupled Termination

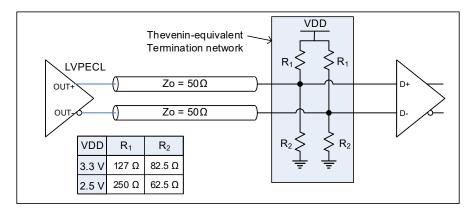


Figure 9. LVPECL DC-coupled Load Termination with Thevenin Equivalent Network

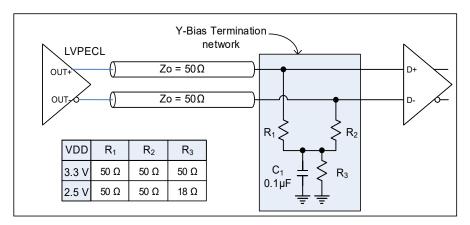


Figure 10. LVPECL with Y-Bias Termination



Termination Diagrams (Continued)

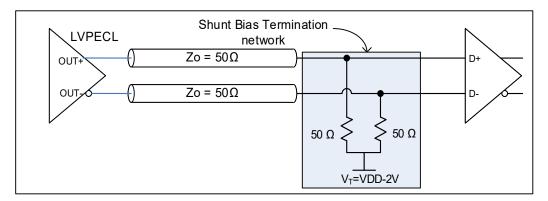


Figure 11. LVPECL with DC-coupled Parallel Shunt Load Termination



Termination Diagrams (Continued)

LVDS:

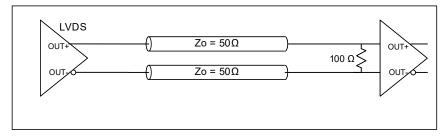


Figure 12. LVDS single DC Termination at the Load

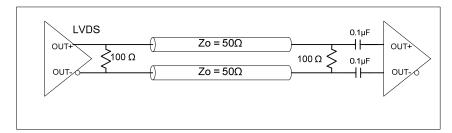


Figure 13. LVDS Double AC Termination with Capacitor Close to the Load

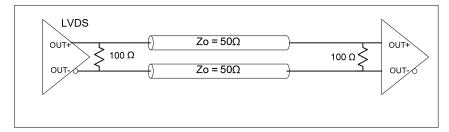


Figure 14. LVDS Double DC Termination



Termination Diagrams (Continued)

HCSL:

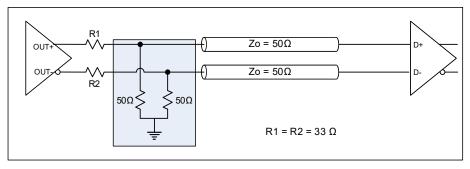
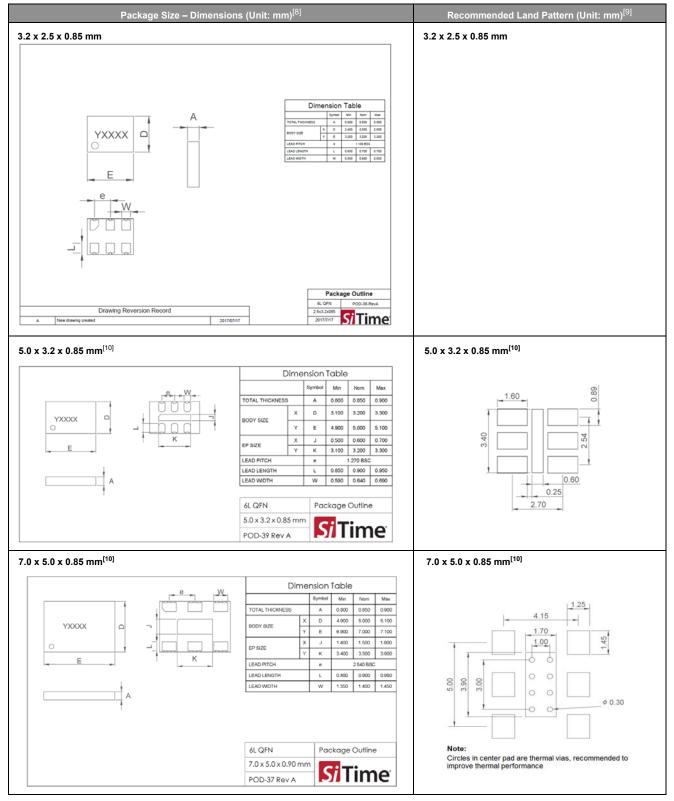


Figure 15. HCSL Interface Termination



Dimensions and Patterns

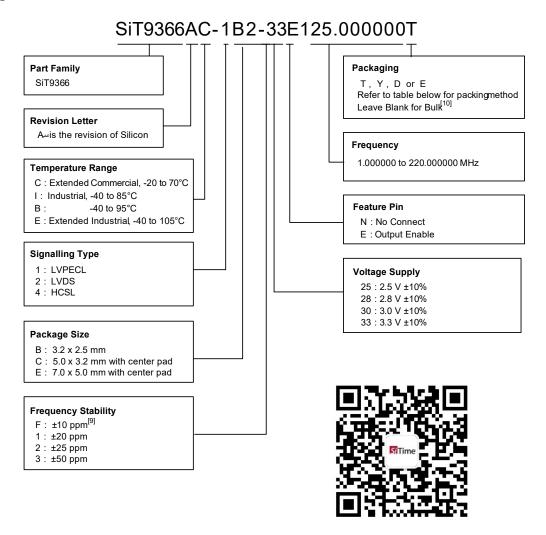


Notes:

- 7. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device
- 8. A capacitor of value 0.1 μF or higher between Vdd and GND is required. An additional 10 μF capacitor between Vdd and GND is required for the best phase jitter performance
- 9. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



Ordering Information



Notes:

9. Contact SiTime for ±10 ppm option

10. Bulk is available for sampling only

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Table 10. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	_	_			Т	Y
5.0 x 3.2			Т	Υ		
3.2 x 2.5	D	Е				



Table 11. Additional Information

Document	Description	Download Link
ECCN #: EAR99	Five character designation used on the commerce Control List (CCL) to identify dual use items for export control purposes.	
Part number Generator	Tool used to create the part number based on desired features.	_
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	http://www.sitime.com/component/docman/doc_download/243-manufacturing-notes-for-sitime-oscillators
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes



Table 3. Revision History

Revision	Release Date	Change Summary
1.0	09/06/2017	Final release
1.04	4/17/18	Added 5032 package. Added -40 to 95C and -40 to 105C temperature ranges Corrected minor errors Added Additional Information Table.
1.05	5/11/2018	Updated Ordering Information and performed minor edits.



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